

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	1.2mΩ@10V	370A



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

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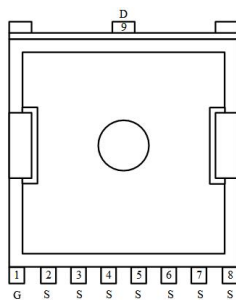
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

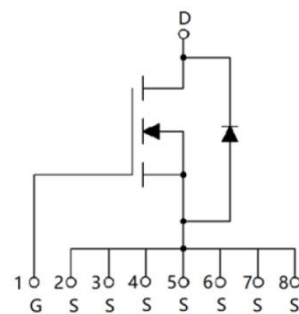
- PWM Application
- Hard switched and high frequency circuits
- Power Management

Package

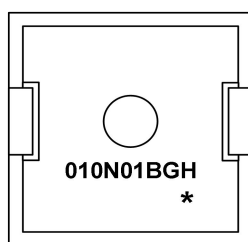


TOLL

Circuit diagram



Marking



010N01BGH : Product code
* : Month code

Order Information

Device	Package	Unit/Tape
SP010N01BGHTO	TOLL	2000

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current1 (Tc=25°C)	I_D	370	A
Continuous Drain Current1 (Tc=100°C)	I_D	247	A
Pulsed Drain Current	I_{DM}	1480	A
Single Pulse Avalanche Energy ¹	E_{AS}	2304	mJ
Power Dissipation (Tc=25°C)	P_D	410	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.3	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

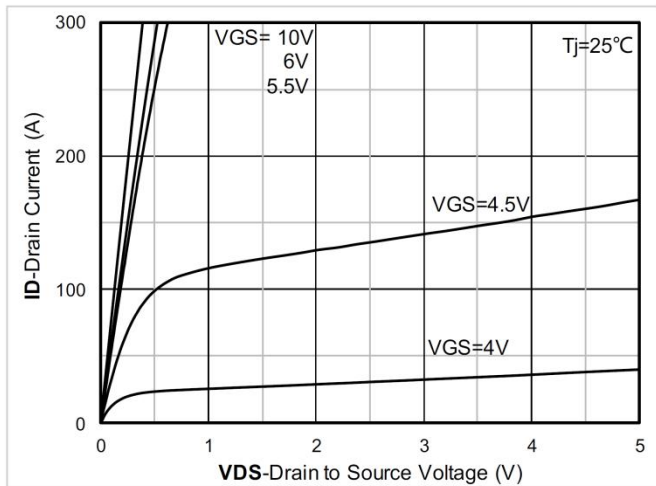
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	100	110	-	V
Drain Cut-Off Current	IDSS	VDS=80V , VGS=0V , TJ=25℃	-	-	1	μA
Gate Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID =250uA	2	3	4	V
Drain-Source ON Resistance	RDS(ON)	VGS=10V , ID=125A	-	1.2	1.5	mΩ
Dynamic Characteristics						
Input Capacitance	Ciss	VDS=50V , VGS=0V , f=1MHz	-	14658	-	pF
Output Capacitance	Coss		-	2335	-	
Reverse Transfer Capacitance	Crss		-	39	-	
Total Gate Charge	Qg	VDS=50V , VGS=10V , ID=125A	-	208	-	nC
Gate-Source Charge	Qgs		-	56	-	
Gate-Drain Charge	Qgd		-	37	-	
Switching Characteristics						
Turn-On Delay Time	td(on)	VDD=50V, VGS=10V , RG=1.6Ω, ID=125A	-	25	-	nS
Rise Time	tr		-	75	-	
Turn-Off Delay Time	td(off)		-	89	-	
Fall Time	tf		-	29	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	VSD	IS = 1A, VGS = 0V	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	370	A
Reverse Recovery Time	Trr	IS=100A, di/dt=100A/us, TJ=25℃	-	92	-	nS
Reverse Recovery Charge	Qrr		-	302	-	nC

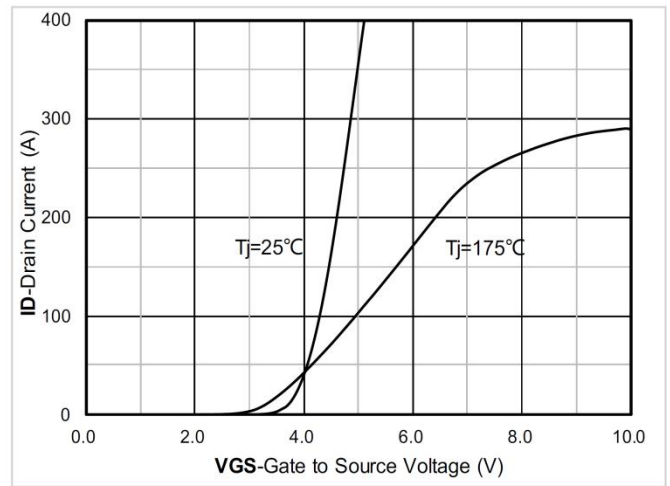
Note :

1. The test condition is $V_{DD}=50V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$

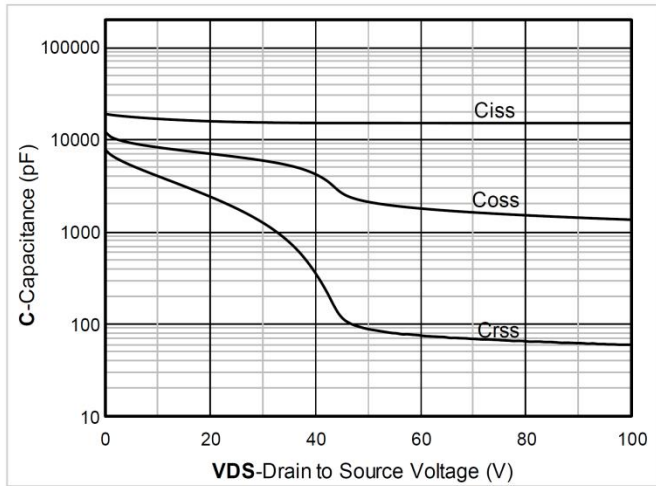
Typical Characteristics



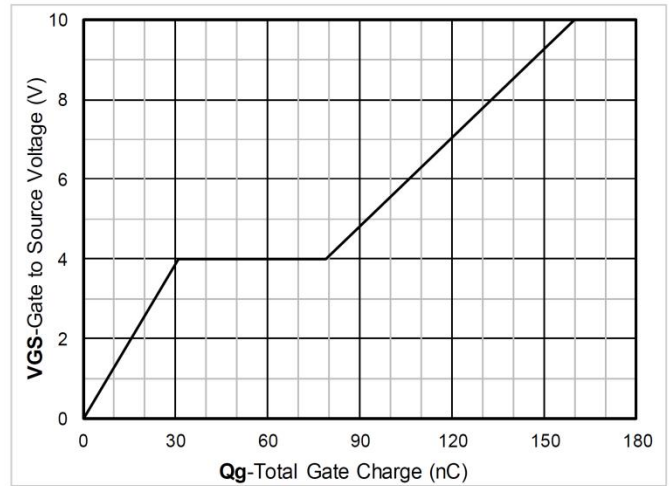
Output Characteristics



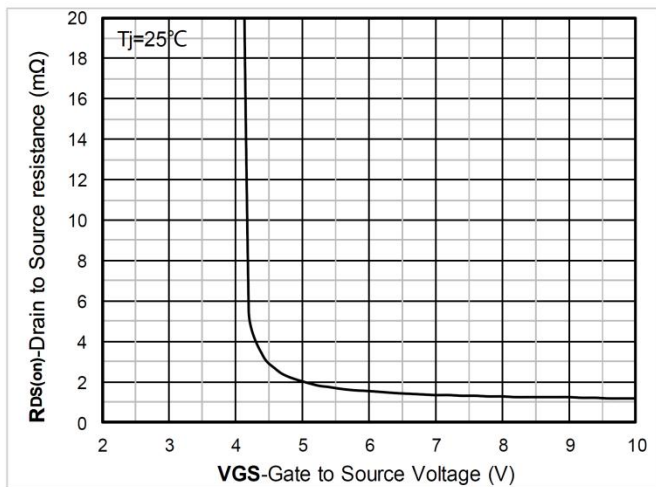
Transfer Characteristics



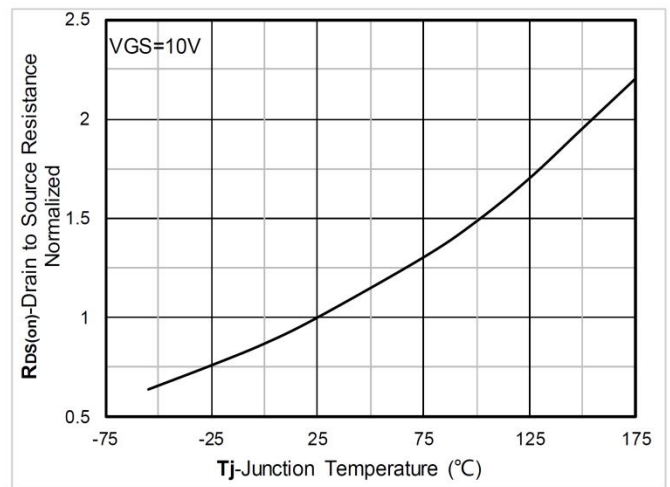
Capacitance Characteristics



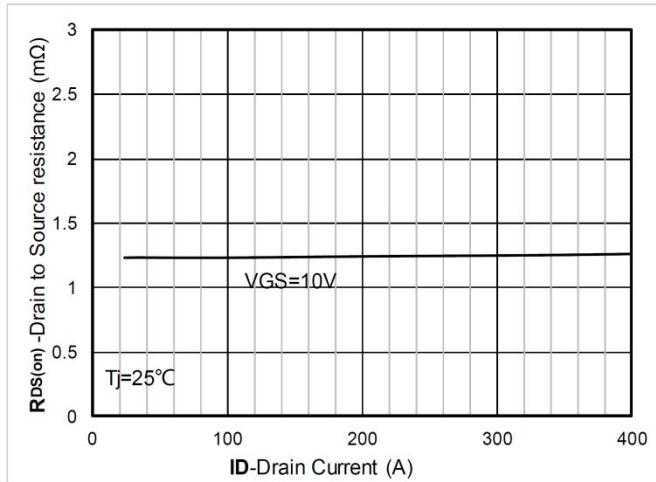
Gate Charge



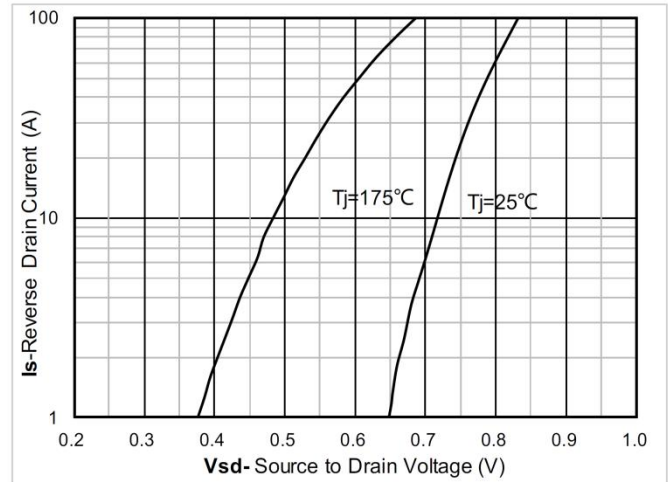
On-Resistance vs Gate to Source Voltage



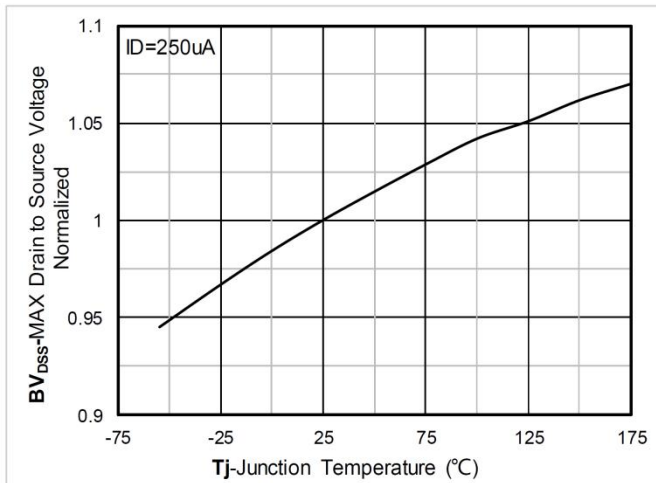
Normalized On-Resistance



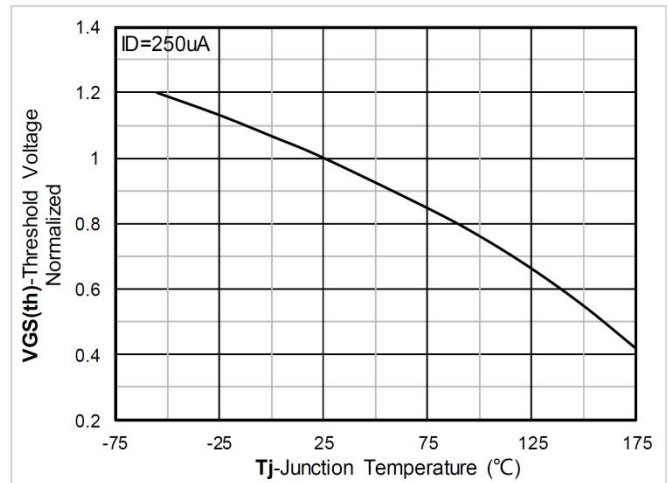
$R_{DS(on)}$ VS Drain Current



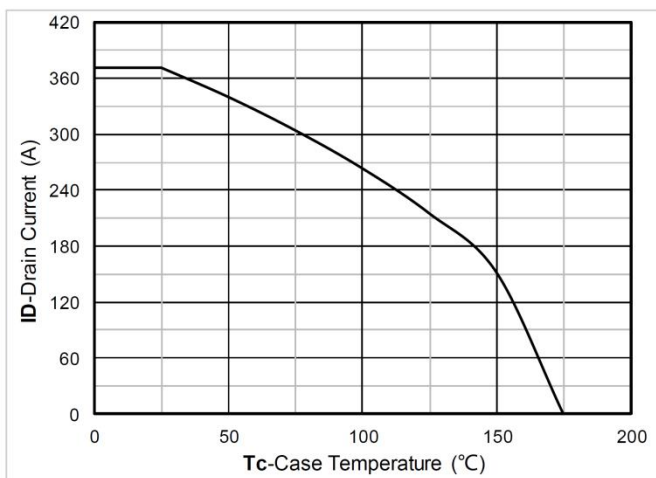
Forward characteristics of reverse diode



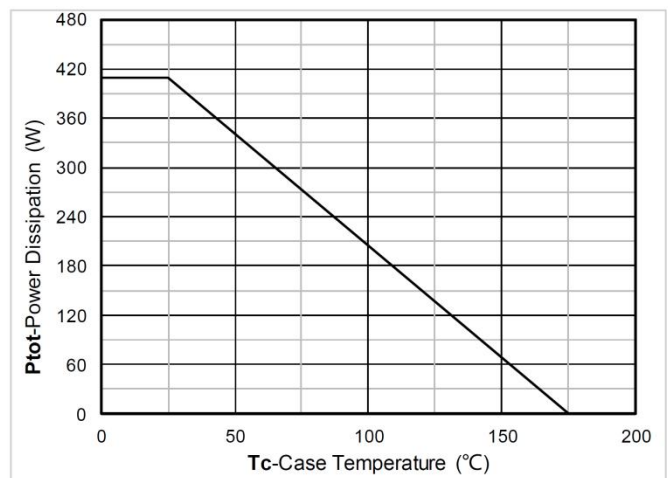
Normalized breakdown voltage



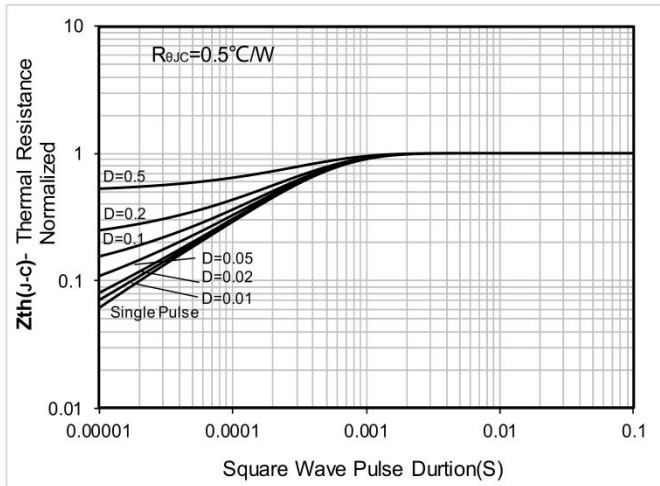
Normalized Threshold voltage



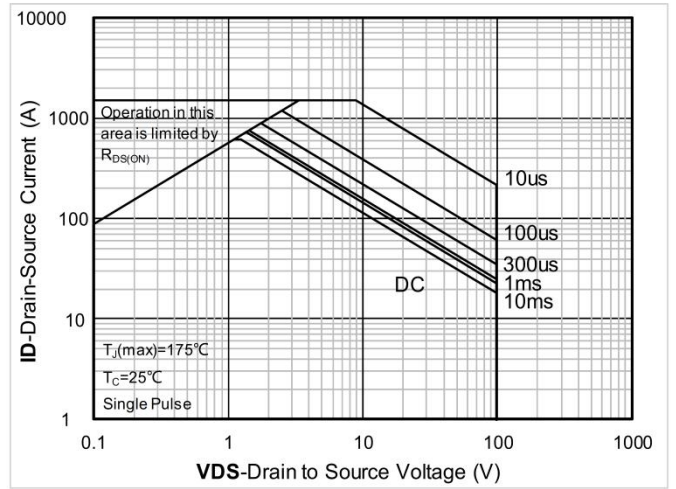
Current dissipation



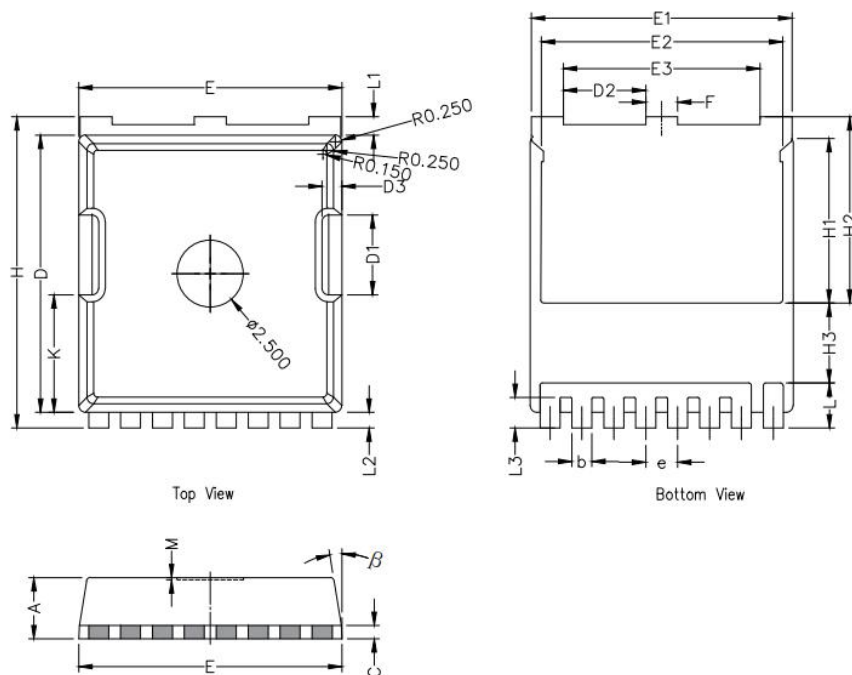
Power dissipation



Maximum Transient Thermal Impedance



Safe Operation Area

TOLL Package Information


Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	2.20	2.30	2.40
b	0.65	0.75	0.85
C	0.508 REF		
D	10.25	10.40	10.55
D1	2.85	3.00	3.15
E	9.75	9.90	10.05
E1	9.65	9.80	9.95
E2	8.95	9.10	9.25
E3	7.25	7.40	7.55
e	1.20 BSC		
F	1.05	1.20	1.35
H	11.55	11.70	11.85
H1	6.03	6.18	6.33
H2	6.85	7.00	7.15
H3	3.00 BSC		
L	1.55	1.70	1.85
L1	0.55	0.7	0.85
L2	0.45	0.6	0.75
M	0.08 REF.		
β	8°	10°	12°
K	4.25	4.40	4.55